U.S. Department of Commerce, Patent and Trademark Office	Atty Docket No.	Serial No.
	M-15230 US	10/632,154
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Applicant	
(Use several sheets if necessary)	Yi Ding	
	Filing Date	Group
	July 30, 2003	Unassigned 2823

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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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							Translation	
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KN	AM	United States Patent Application No. 10/798,475, entitled "Fabrication of Conductive Lines Interconnecting Conductive Gates in Nonvolatile Memories and Non-Volatile Memory Structures," Filed on March 10, 2004; Attorney Docket No. M-15296 US.
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Examiner K Nguyen	Date Considered 07/23/04

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KN	AT	United States Patent Application No. 10/440,005, entitled "Fabrication of Dielectric On A Gate Surface To Insulate The Gate From Another Element Of An Integrated Circuit," Filed on May 16, 2003; Attorney Docket No.: M-15203 US.
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KN	AV	United States Patent Application No. 10/440,500, entitled "Integrated Circuits With Openings that Allow Electrical Contact To Conductive Features Having Self-Aligned Edges," Filed on May 16, 2003; Attorney Docket No.: M-15205 US.
KN	AW	United States Patent Application No. 10/393,212, entitled "Nonvolatile Memories And Methods Of Fabrication," Filed on March 19, 2003; Attorney Docket No.: M-12902 US.
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KN	BB	United States Patent Application No. 10/632,007, entitled "Arrays Of Nonvolatile Memory Cells Wherin Each Cell Has Two Conductive Floating Gates," Filed on July 30, 2003; Attorney Docket No.: M-15223 US.
KN	BC	United States Patent Application No. 10/631,452, entitled "Fabrication Of Dielectric For A Nonvolatile Memory Cell Having Multiple Floating Gates," Filed on July 30, 2003; Attorney Docket No.: M-15229 US.
KN	BD	United States Patent Application No. 10/631,552, entitled "Nonvolatile Memories And Methods Of Fabrication," Filed on July 30, 2003; Attorney Docket No.: M-12902-1P US.
KN	BE	United States Patent Application No. 10/632,186, entitled "Nonvolatile Memory Cell With Multiple Floating Gates Formed After The Select Gate And Having Upward Protrusions," Filed on July 30, 2003; Attorney Docket No.: M-15241 US.
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